

# **PNP** Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

# Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current - Continuous	1.2	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These resteady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic		Max		Units
		MPSA64	*MMBTA64	**PZTA64	
P <sub>D</sub>	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

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# **PNP** Darlington Transistor (continued)

	ical Characteristics TA=2	5°C unless otherwise noted	-	1	1
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
OFF CHAI	RACTERISTICS Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 100 μA, I <sub>B</sub> = 0	30	I	V
		$I_{C} = 100 \ \mu A, I_{B} = 0$ $V_{CB} = 30 \ V, I_{E} = 0$	30	100	V nA

# **ON CHARACTERISTICS\***

ON CHAR	ACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		
		$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	20,000		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$		1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 5.0 V		2.0	V

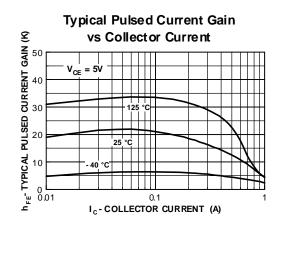
# SMALL SIGNAL CHARACTERISTICS

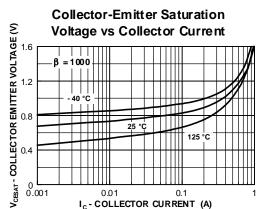
f <sub>T</sub> Current Gain - Bandwidth Product	$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5.0 V, f = 100 MHz	125	MHz
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\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

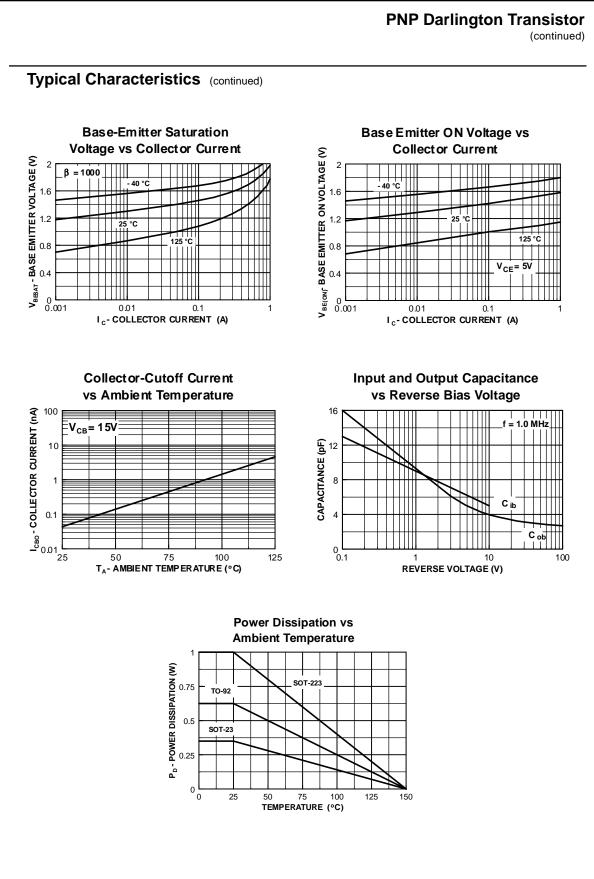




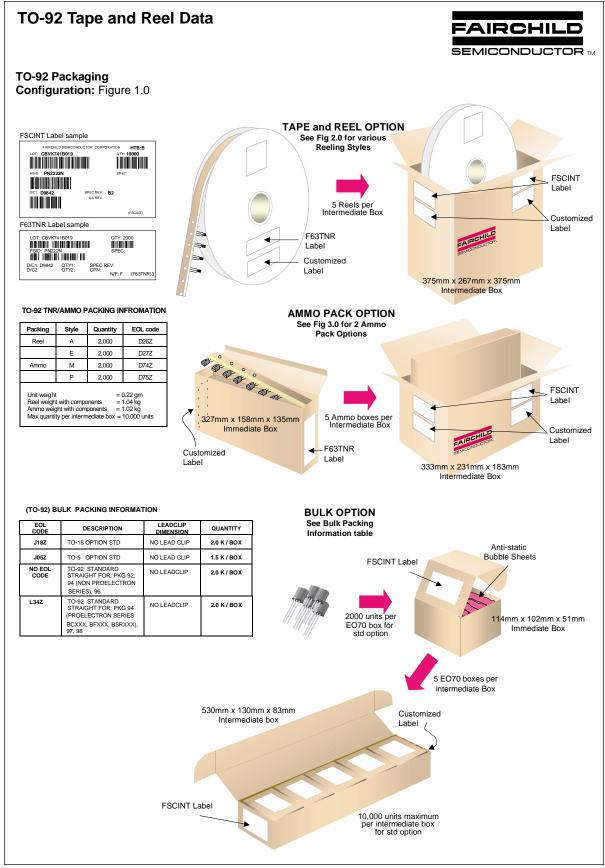


#### 0.001 0.01 0.1 I<sub>c</sub>-COLLECTOR CURRENT (A)

MPSA64 / MMBTA64 / PZTA64

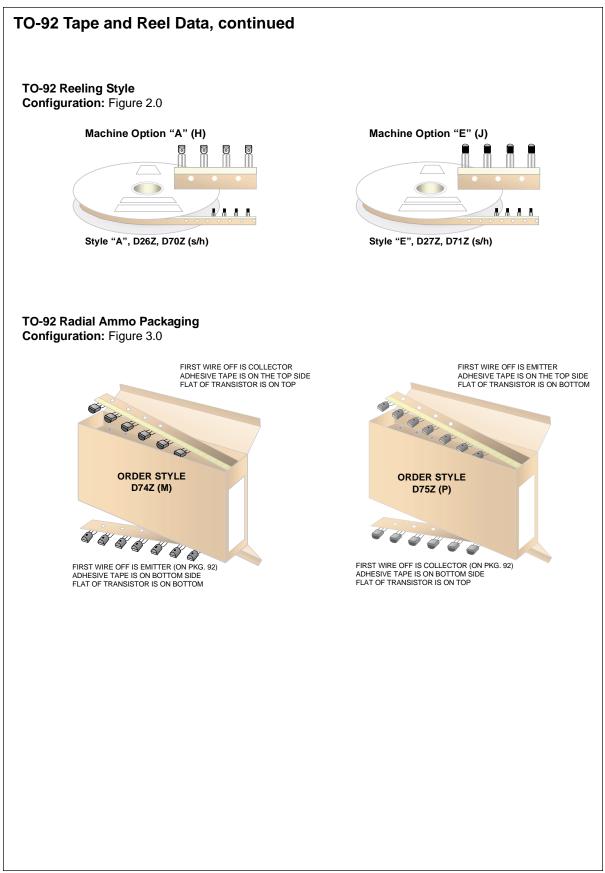


# MPSA64 / MMBTA64 / PZTA64

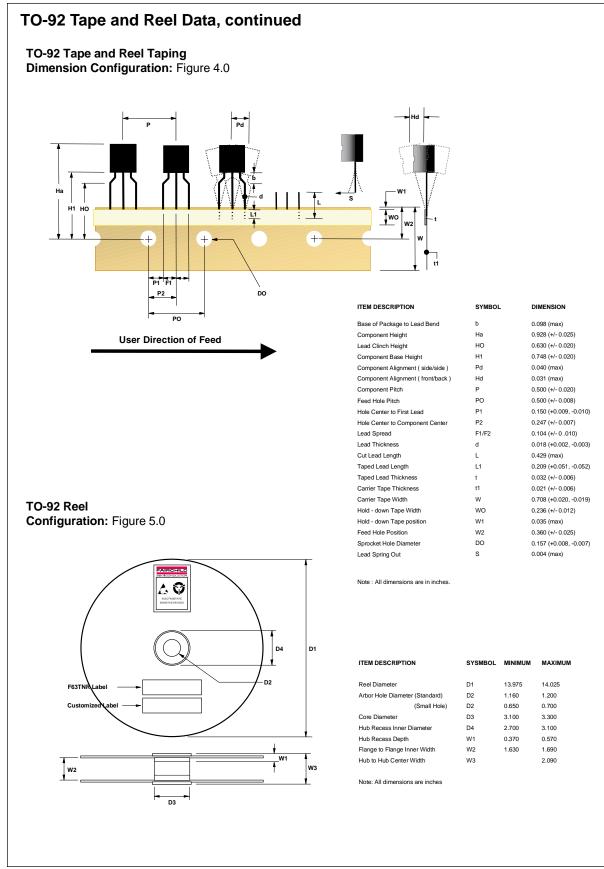


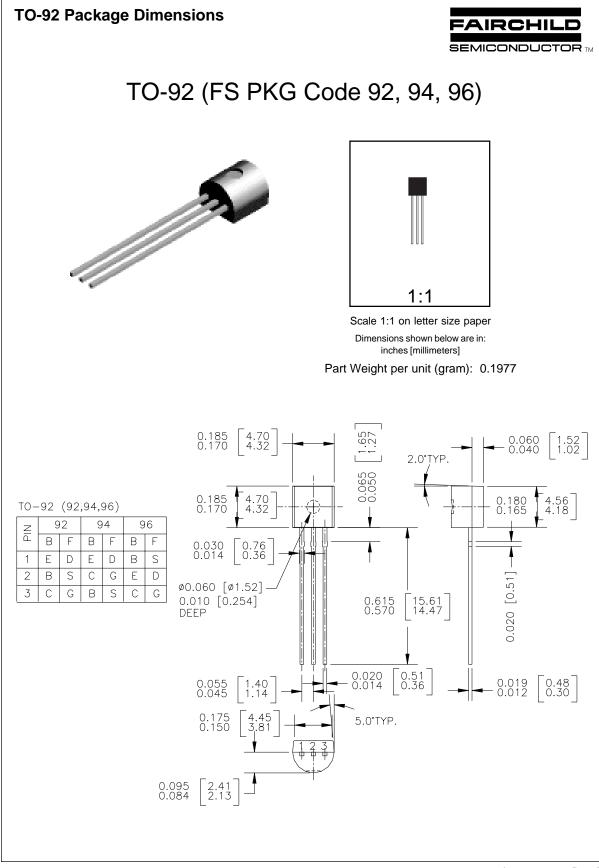
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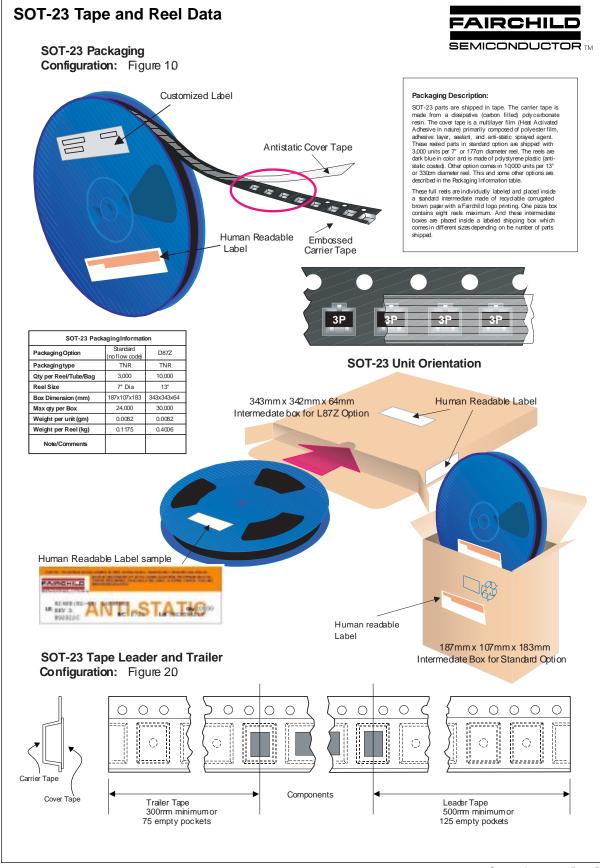
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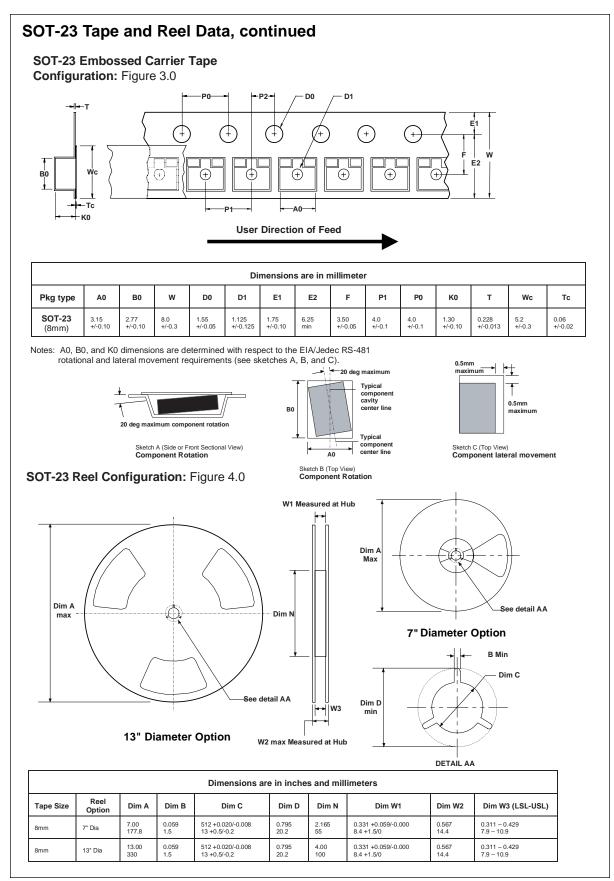
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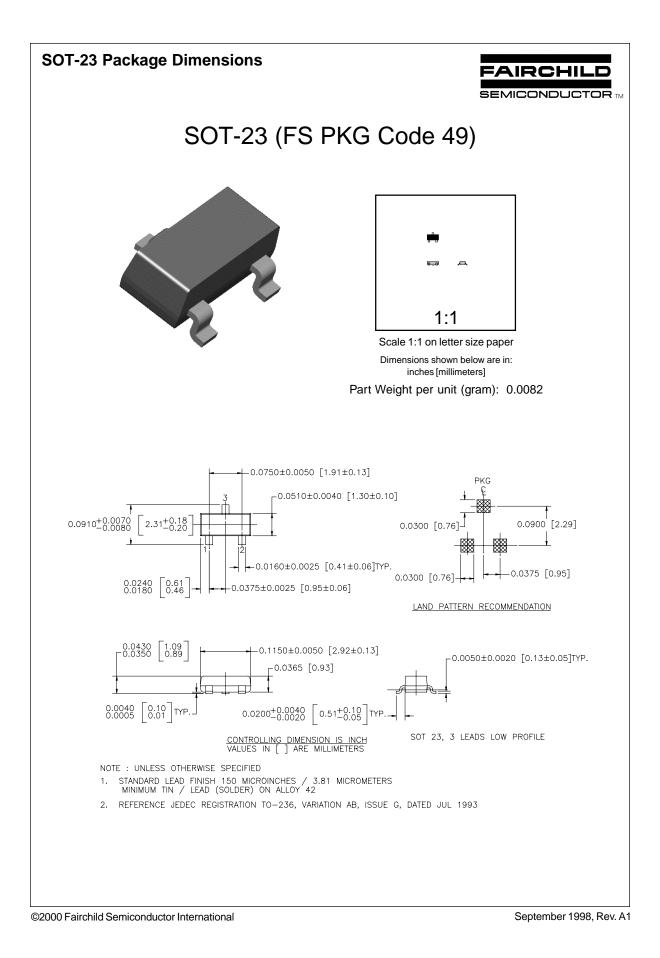


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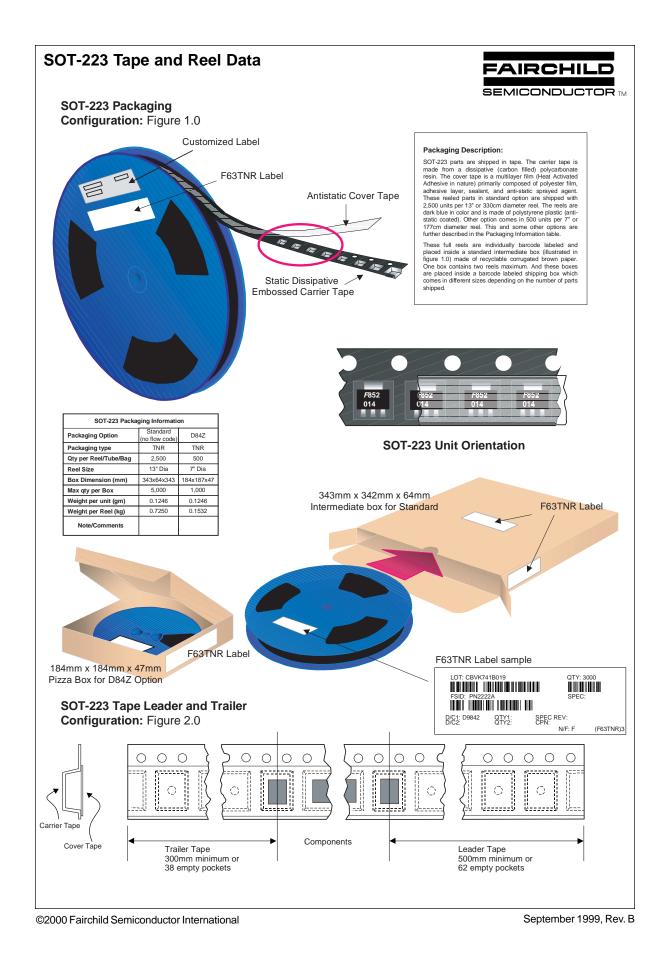
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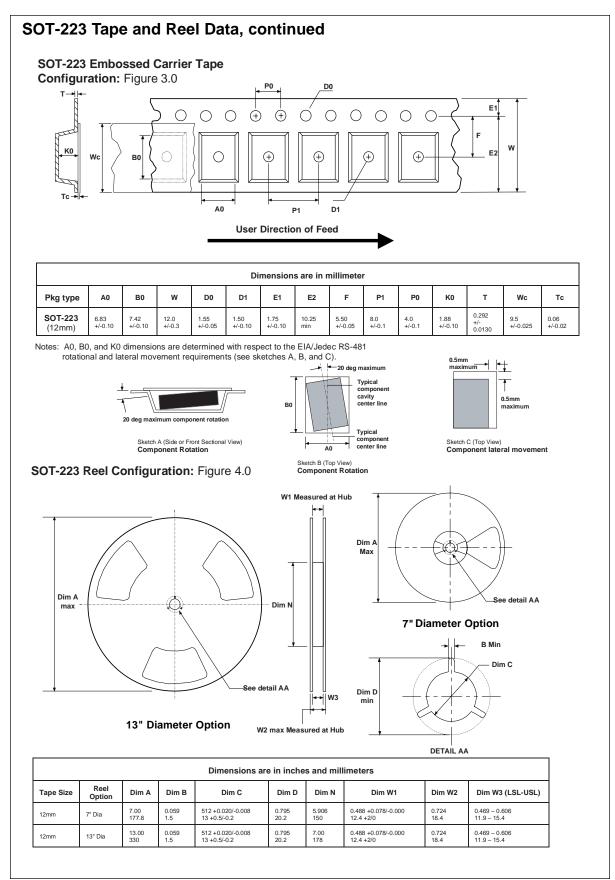
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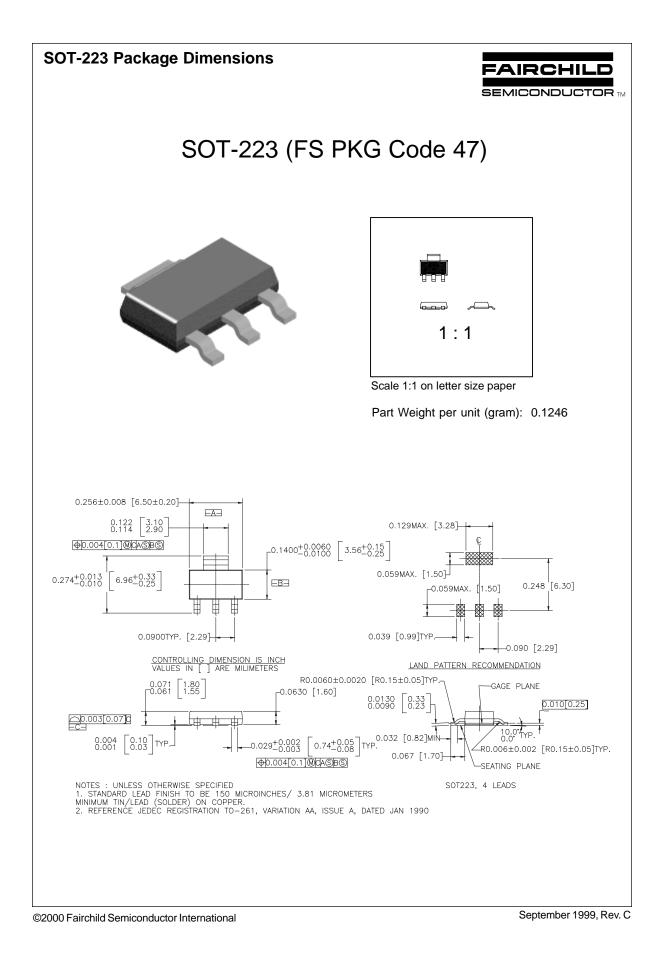
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